

# Three-quadrant triacs high commutation Rev. 03 — 24 May 2005

**Product data sheet** 



## 1.1 General description

Passivated high commutation triac in a SOT428 (DPAK) plastic package. Intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commutate the full rated RMS current at the maximum rated junction temperature, without the aid of a snubber.

## 1.2 Features

- High maximum junction temperature
- High commutation capability

## 1.3 Applications

Motor control

Industrial and domestic heating

#### 1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BTA204S-600B)}$
- V<sub>DRM</sub> ≤ 600 V (BTA204S-600C)
- $I_{TSM} \le 25 \text{ A}$

- V<sub>DRM</sub> ≤ 800 V (BTA204S-800B)
- V<sub>DRM</sub> ≤ 800 V (BTA204S-800C)
- $I_{T(RMS)} \le 4 A$

## **Pinning information**

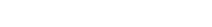
Table 1: **Pinning** 

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		<b>.</b> .
2	main terminal 2 (T2)	mb 	T2—T1
3	gate (G)		sym051
mb	mounting base	[1]	
		レ <sup>2</sup> ゼ 1 3	
		SOT428 (DPAK)	

[1] Connected to main terminal 2 (T2)







**Ordering information** 

#### **Table 2: Ordering information**

Type number	Package		
	Name	Description	Version
BTA204S-600B	DPAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428
BTA204S-600C			
BTA204S-800B	_		
BTA204S-800C			

# 4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage	BTA204S-600B; BTA204S-600C	<u>[1]</u> _	600	V
		BTA204S-800B; BTA204S-800C	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107  ^{\circ}C$ ; see Figure 4 and 5	-	4	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	25	А
		t = 16.7 ms	-	27	А
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10 ms	-	3.1	A <sup>2</sup> s
dl <sub>T</sub> /dt	repetitive rate of rise of on-state current after triggering	$I_{TM} = 6 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/μs
I <sub>GM</sub>	peak gate current		-	2	Α
$V_{GM}$	peak gate voltage		-	5	V
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

<sup>[1]</sup> Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.

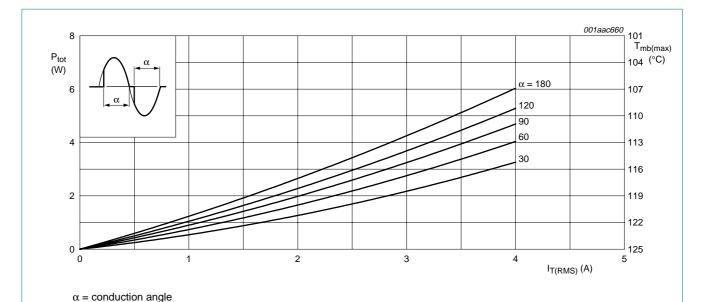


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

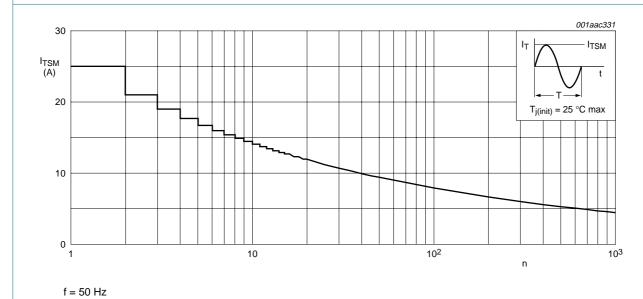
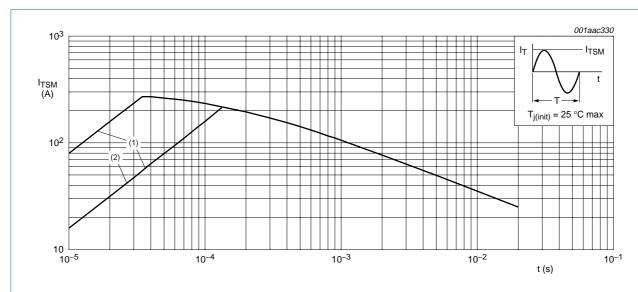


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal cycles; maximum values

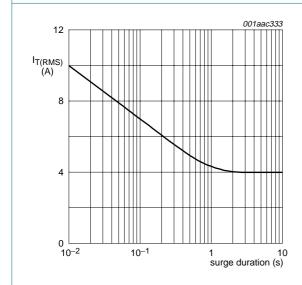
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 $t_p \le 20 \text{ ms}$ 

- (1) dl<sub>T</sub>/dt limit
- (2) T2- G+ quadrant

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



 $f = 50 \text{ Hz}; T_{mb} \le 107 \,^{\circ}\text{C}$ 



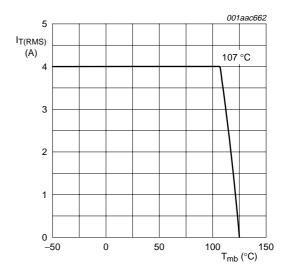


Fig 5. RMS on-state current as a function of mounting base temperature



## 5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from	full cycle	-	-	3.0	K/W
	junction to mounting base	half cycle	-	-	3.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed-circuit board (FR4) mounted as in Figure 13	-	75	-	K/W

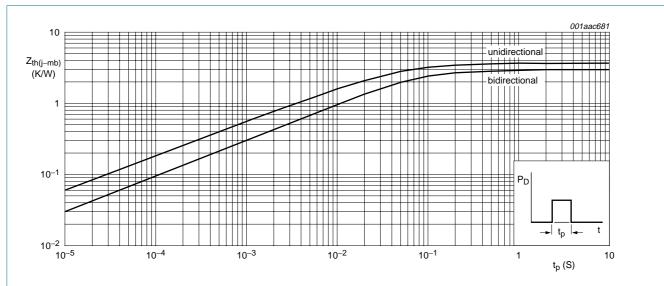


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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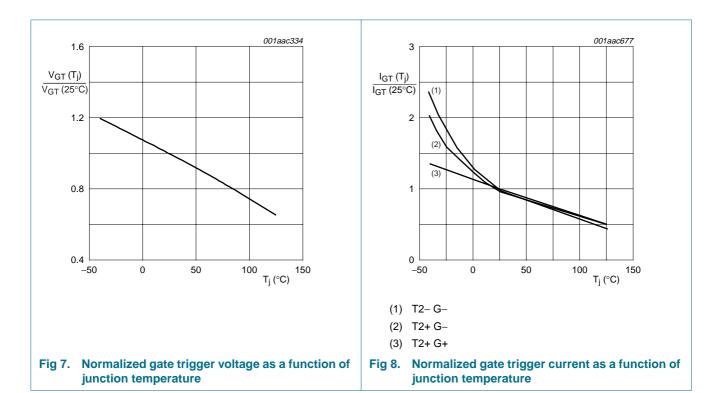
## 6. Static characteristics

Table 5: Static characteristics

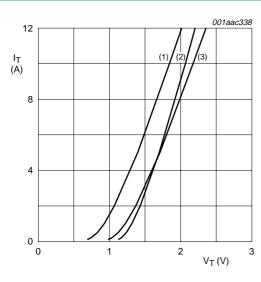
 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter Conditions			BTA204S-600B BTA204S-800B			BTA204S-600C BTA204S-800C			Unit
				lin	Тур	Max	Min	Тур	Max	
$I_{GT}$	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A see } \frac{\text{Figure 8}}{}$	1			'		•		
		T2+ G+			-	50	-	-	35	mΑ
		T2+ G-	-		-	50	-	-	35	mΑ
		T2- G-	-		-	50	-	-	35	mΑ
IL	latching current	V <sub>D</sub> = 12 V; I <sub>GT</sub> = 0.1 A; see <u>Figure 10</u>								
		T2+ G+	-		-	30	-	-	20	mΑ
		T2+ G-	-		-	45	-	-	30	mΑ
		T2- G-	-		-	30	-	-	20	mΑ
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; I <sub>GT</sub> = 0.1 A; see <u>Figure 11</u>	-		-	30	-	-	20	mΑ
$V_{T}$	on-state voltage	I <sub>T</sub> = 5 A; see <u>Figure 9</u>	-		1.4	1.7	-	1.4	1.7	V
$V_{GT}$	gate trigger	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; see <u>Figure 7</u>	-		0.7	1.5	-	0.7	1.5	V
	voltage	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.2	25	0.4	-	0.25	0.4	-	V
I <sub>D</sub>	off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125  ^{\circ}C$	-		0.1	0.5	-	0.1	0.5	mA

[1] Device does not trigger in the T2- G+ quadrant.



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 $V_O$  = 1.27 V;  $R_S$  = 0.091  $\Omega$ 

- (1)  $T_i = 125 \,^{\circ}\text{C}$ ; typical values
- (2)  $T_i = 25 \,^{\circ}C$ ; maximum values
- (3)  $T_j = 125 \,^{\circ}C$ ; maximum values

Fig 9. On-state current as a function of on-state voltage; typical values

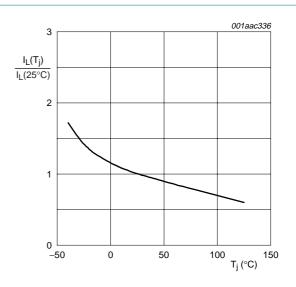


Fig 10. Normalized latching current as a function of junction temperature

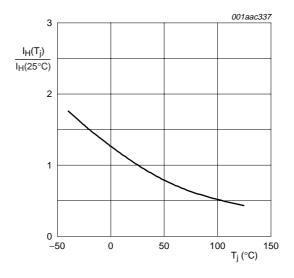


Fig 11. Normalized holding current as a function of junction temperature

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## 7. Dynamic characteristics

Table 6: Dynamic characteristics

 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	BTA204S-600B BTA204S-800B			BTA204S-600C BTA204S-800C			Unit
			Min	Тур	Max	Min	Тур	Max	
dV <sub>D</sub> /dt	critical rate of rise of off-state voltage	$V_{DM} = 0.67V_{DRM(max)};$ $T_j = 125$ °C; exponential waveform; gate open circuit	1000	-	-	1000			V/μs
dl <sub>com</sub> /dt	critical rate of change of commutating current	$V_{DM} = 400 \text{ V; } T_j = 125 \text{ °C;}$ $I_{T(RMS)} = 4A;$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s; gate open}$ circuit	6	-	-	3	-	-	A/ms
t <sub>gt</sub>	gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	-	2	-	μs

## 8. Package information

Refer to mounting instructions for SOT428 (DPAK) package.

Plastic meets requirements of UL94 V-0 at  $\frac{1}{8}$  inch.

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## 9. Package outline

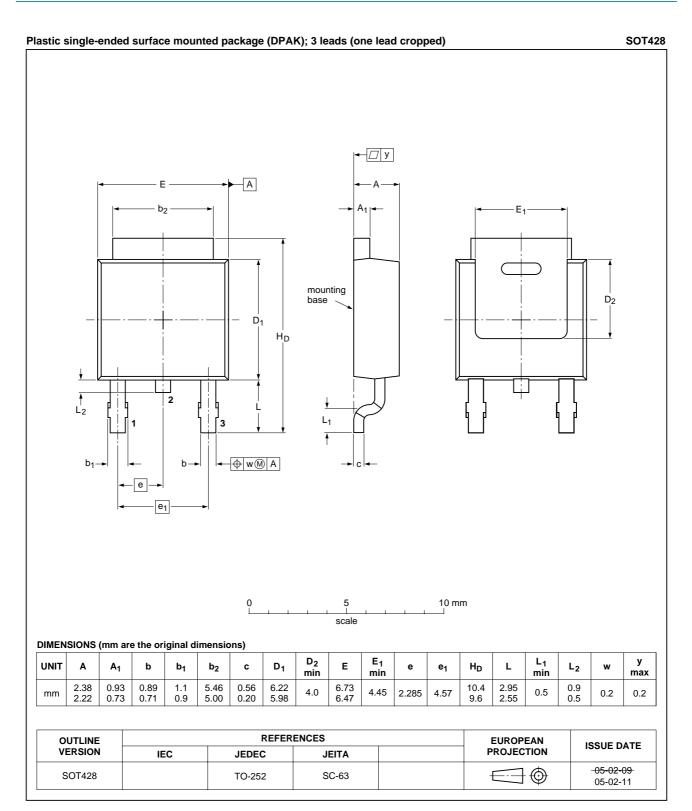


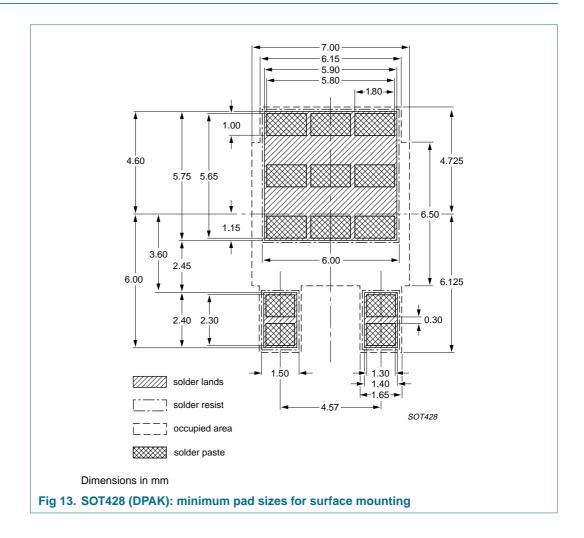
Fig 12. Package outline SOT428 (DPAK)

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## 10. Mounting



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## Table 7: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BTA204S_SER_B_C_3	20050524	Product data sheet	-	9397 750 14862	BTA204S_SERIES_B_C_2
Modifications:	<ul><li>and inforr</li><li>500 V typ</li></ul>	nation standard of Ph	ilips Semic		with the new presentation
BTA204S_SERIES_B_C_2	19981201	Product specification	-	n.a.	BTA204S_SERIES_B_C_1
BTA204S_SERIES_B_C_1	19971001	Objective specification	-	n.a.	-

#### Three-quadrant triacs high communication



Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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# BTA204S series B and C

Three-quadrant triacs high communication

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